

**Response Under 37 CFR 1.116**  
**Expedited Procedure**  
**Examining Group 1700**  
Application No. 10/820,994  
Paper Dated: June 9, 2008  
In Reply to USPTO Correspondence of April 7, 2008  
Attorney Docket No. 1217-043819

**AMENDMENTS TO THE SPECIFICATION:**

**Please replace the paragraph beginning at page 5, line 11, with the following rewritten paragraph:**

-- Further, in case of treatment with a commercially available solution for dissolving nickel, insufficient cleaning causes ~~remaining~~ of the treated substance to remain on the wiring pattern, and a detrimental influence is rather exerted on the insulation properties.--

**Please replace the paragraph beginning at page 16, line 8, with the following rewritten paragraph:**

-- By treating the film carrier tape under the above conditions prior to plating, metals (nickel, chromium, copper and alloys thereof) which remain on the ~~insulating~~ insulating film between wirings after the pattern etching can be removed almost completely. In the present invention, it is preferable that the film carrier tape having been subjected to the above treatment prior to plating is then treated with an acid treatment solution comprising 50 to 150 g/l of  $K_2S_2O_8$ , 5 to 20 ml/l of  $H_2SO_4$  and 0 to 3 g/l of Cu at a temperature of 20 to 40°C for a period of 5 to 20 seconds and then subjected to plating. --

**Please replace the paragraph beginning at page 19, line 23, with the following rewritten paragraph:**

-- The plating-pretreatment solution of the present invention is particularly preferably used in a process comprising performing pickling using 2-4 N sulfuric acid for 10 to 60 seconds after etching, then heating the film carrier at a temperature of 150 to 200°C for a period of 10 minutes to 3 hours to perform ring closure of ring-opened polyimide produced in the polyimide ~~insulating~~ insulating film, then treating the film carrier with the plating-pretreatment solution of the present invention, performing pickling with an acid treatment solution containing  $K_2S_2O_8$  and  $H_2SO_4$  and then performing tin plating. By performing treatment with the plating-pretreatment solution of the present invention after ring closure of the ring-opened polyimide that is produced on the surface of the polyimide film (i.e., insulating film) by etching, alkaline cleaning, acid cleaning, etc., as described above, migration resistance of the resulting film carrier tape can be remarkably enhanced. --